

L Number	Hits	Search Text	DB	Time stamp
1	78	((430/30).CCLS.) and (wafer with edge)) and (ARC or reflect\$4) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/04 13:21
2	215	((430/311-313,322).CCLS.) and wafer and ((edge with (bead or expos\$4))) and ((ARC or reflect\$5) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/04 13:21
3	13	((356/237.4-237.6).CCLS.) and wafer and ((edge with (bead or expos\$4)) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/04 13:22
4	96	((427/96,145,240).CCLS.) and (resist or photoresist) and (ARC or BARC or reflect\$5)) and ((wafer or substrate) same edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/04 13:22
5	318	((resist or photoresist) and ((wafer or substrate or Silicon) and (edge near (bead\$3 or trim\$4 or expos\$5)))) and ((ARC or reflect\$5) and (resist or photoresist))) and ((wafer or substrate or Silicon) with (edge near (bead\$3 or trim\$4 or expos\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/04 13:23